

**DOT MATRIX DISPLAY**

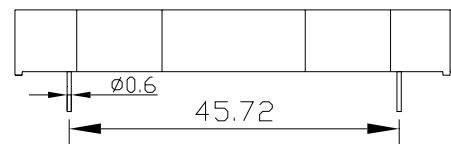
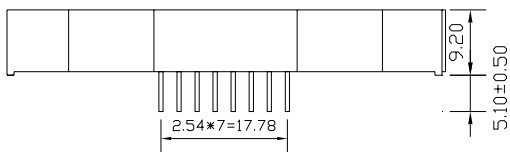
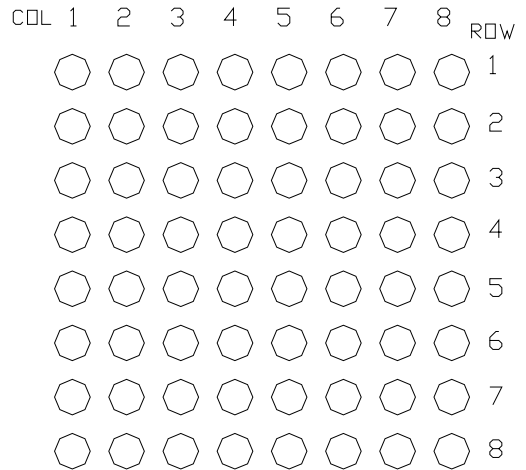
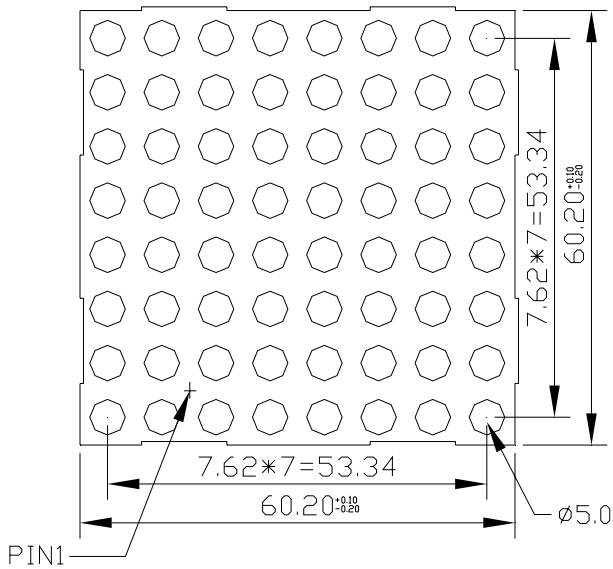
# **JZM23882ASR-GW**

## **DATA SHEET**

**DOCUMENT NO.: WI-RD-LDS-15882ASR-GW****RELEASE DATE: 2007-4-20****VERSION: A/0****RD No.: JZD20070420001**

# PART NO.: JZM23882ASR-GW

## Package Dimensions



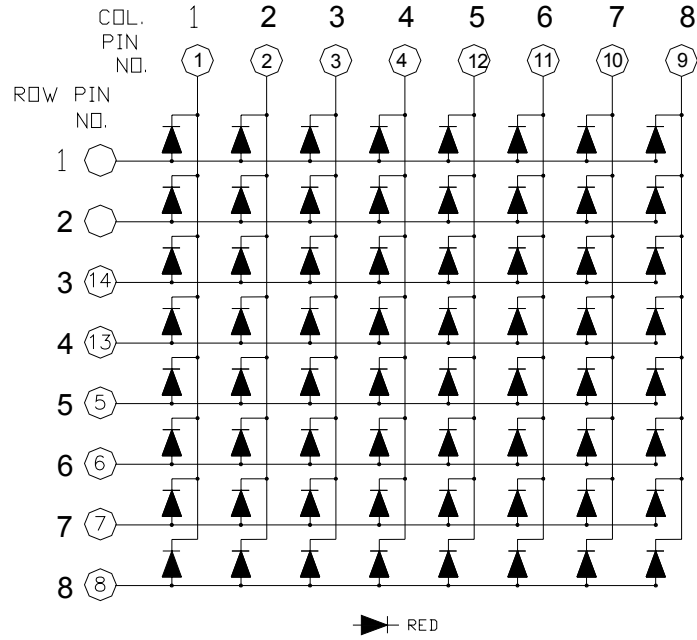
### Notes:

1. All dimension are in millimeters and(Inch)tolerance is  $\pm 0.25\text{mm}$  unless otherwise noted.
2. Specifications are subject to change without notice.

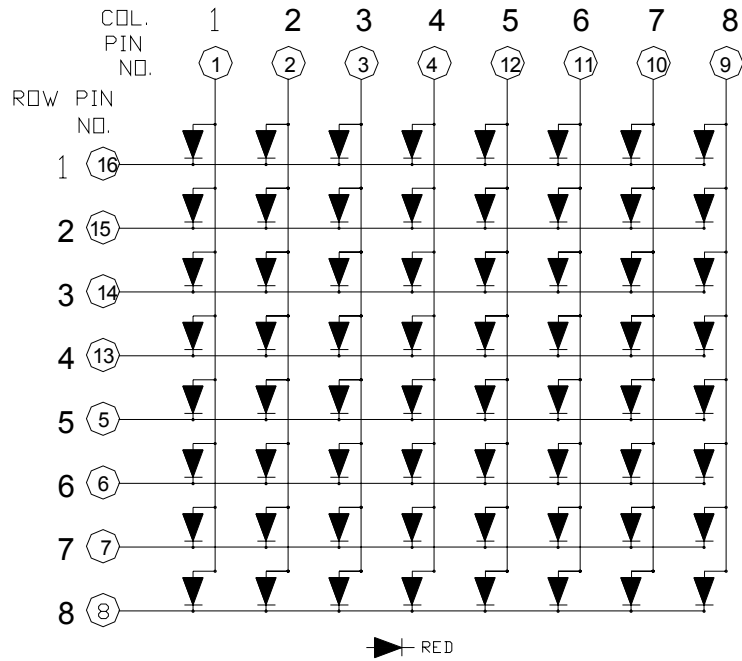
# PART NO.: JZM23882ASR-GW

## Internal Circuit Diagram

### JZM23882ASR-GW



### JZM23882BSR-GW



**PART NO.: JZM23882ASR-GW****Electrical Connection**

PIN NO.	JZM23882ASR-GW	PIN NO.	JZM23882BSR-GW
1	Anode Row 5	1	Cathode Row 5
2	Anode Row 7	2	Cathode Row 7
3	Cathode Column 7	3	Anode Column 7
4	Cathode Column 6	4	Anode Column 6
5	Anode Row 8	5	Cathode Row 8
6	Cathode Column 4	6	Anode Column 4
7	Anode Row 6	7	Cathode Row 6
8	Anode Row 3	8	Cathode Row 3
9	Anode Row 1	9	Cathode Row 1
10	Cathode Column 5	10	Anode Column 5
11	Cathode Column 3	11	Anode Column 3
12	Anode Row 4	12	Cathode Row 4
13	Cathode Column 8	13	Anode Column 8
14	Anode Row 2	14	Cathode Row 2
15	Cathode Column 2	15	Anode Column 2
16	Cathode Column 1	16	Anode Column 1

**Absolute Maximum Rating at=Ta=25□**

Parameter	Symbol	Ratings	UNIT
		SGM	
Forward Current Per Chip	IF	30	mA
Peak Forward Current Per Chip*1	IFP	100	mA
Power Dissipation Per Chip	PD	100	mW
Reverse Current Per Any Chip	Ir	50	uA
Electrostatic Discharge*2	ESD	1000	V
Operating Temperature	Topr	-25~+85	□
Storage Temperature	Tstg	-25~+85	□

Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260□

\*1:Duty 1/10,0.1ms Pulse With

\*2:Static Electricity or power surge will damage the LED. Use of a conductive wrist band or anti-electrosatic glove is recommended when handing these LED. All devices, equipment and machinery must be properly grounded.

**PART NO.: JZM23882ASR-GW****Part selection And Application Information(Ratings at 25□)**

PART NO.	COLOR □ EPOX Y/SURF ACE□	CHIP		Common cathode or anode	WD (nm )	Electrical				IV- M
		Material	Emitted			Vf(v)		Iv(mcd)		
						Typ.	Max.	Min.	Typ.	
JZM23882ASR-GW	WHITE DIFFUS E/GRAY	AlGaInP	RED	Common anode	630	2.1	2.4	60	70	1 □ 1.1

Note:1.The forward voltage data did not including±.01V testing tolerance.

2.The luminous intensity data did not including±15% testing tolerance.

**Test Condition For Each Parameter**

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=20mA
Peak Wavelength	WP	nm	If=20mA
Dominant Wavelength	WD	nm	If=20mA
Spectral Line Half-Width	▲W	nm	If=20mA
Reverse Current Any Chip	Ir	μA	If=20mA
Luminous Intensity Matching Ratio	IV-M		

# Typical Optical-Electronic Characteristic Curves

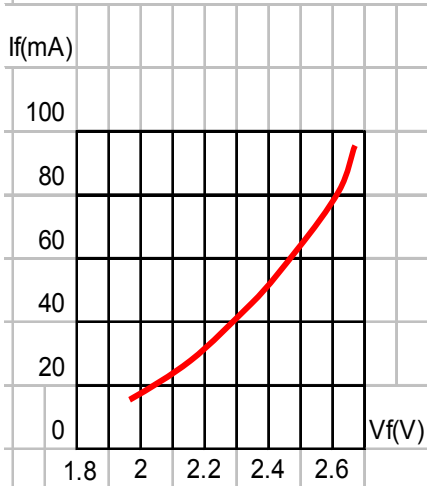


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE.

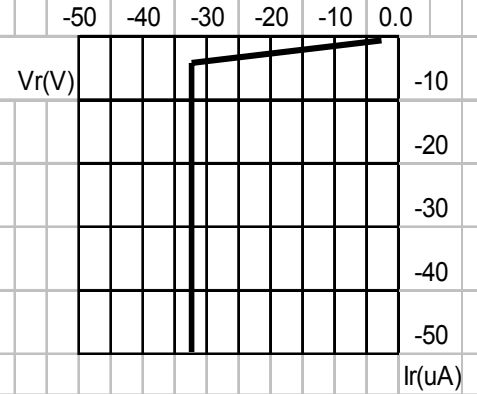
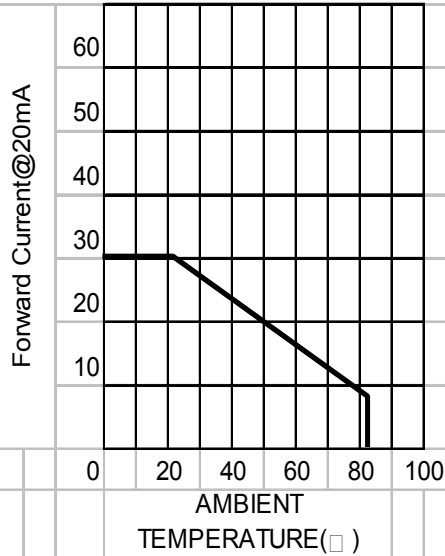


Fig.2 REVERSE CURRENT VS. REVERSE VOLTAGE.

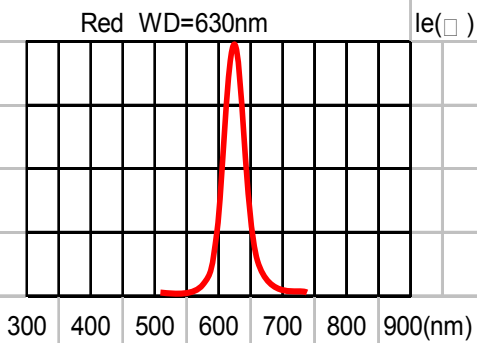


Fig.4 RELATIVE LUMINOUS INTENSITY VS. WAVELENGTH.

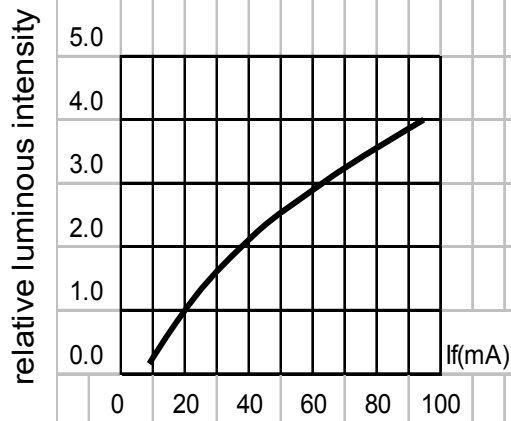


Fig.3 RELATIVE LUMINOUS INTENSITY VS. FORWARD

## Soldering Condition (Pb-Free)

### 1. Iron:

Soldering Iron: 30W Max

Temperature 350°C Max

Soldering Time: 3 Seconds Max (One time only)

Distance: Solder Temperature 1/16Inch Below Seating Plane

For 3 Seconds At 260°C

### 2. Wave Soldering Profile

Dip Soldering

Preheat: 120°C Max

Preheat time: 60 seconds Max

Ramp-up

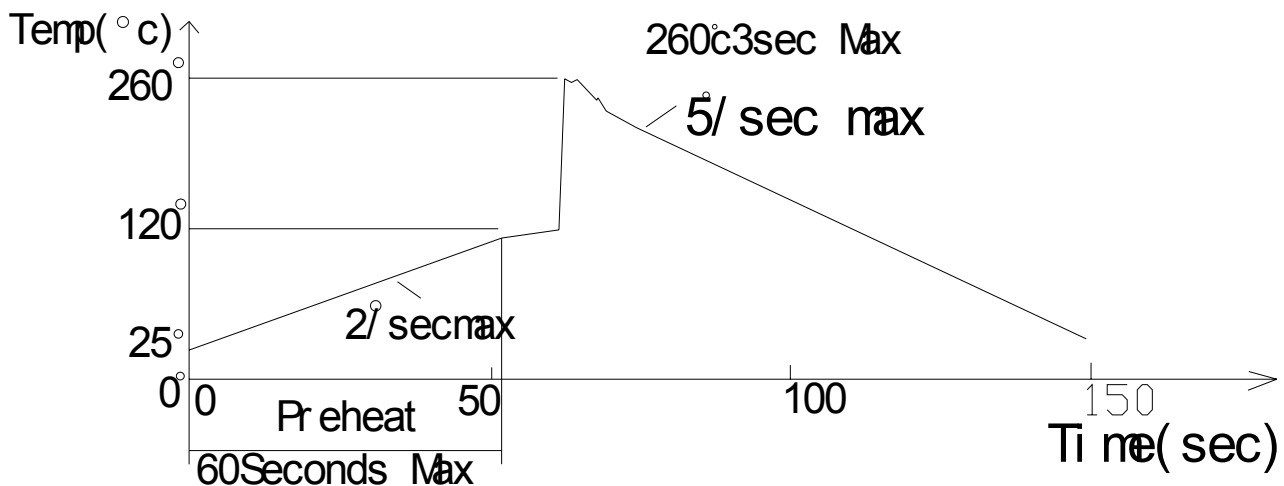
2°C/sec(max)

Ramp-Down: -5°C/sec(max)

Solder Bath: 260°C Max

Dipping Time: 3 seconds Max

Distance: Solder Temperature 1/16Inch Below Seating Plane for 3 Seconds At 260°C



Note: 1. Wave solder should not be made more than one time.

2. You can just only select one of the soldering conditions as above.

## Reliability Test:

Test Item	Standard Test Method	Test Condition	Description
Operating Life Test	JIS C7021:B-1 MIL-STD-750:1026 MIL-STD-883:1005	1. Under Room Temperature 2. If=10 mA 3. t=1000hrs(-24hrs,+72hrs)	This test is conducted for the purpose of deteming the resistance of a part in electrical and themal stressed.
High Temperature Storage Test	JIS C 7021:B-10 MIL-STD-883:1008	1. Ta=105□±5□ 2. t=1000hrs(-24hrs,+72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.
Low Temperature Storage Test	JIS C 7021:B-12	1. Ta=-40□±5□ 2. t=1000hrs(-24hrs,+72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.
High Temperature High Humidity Test	JIS C 7021:B-11 MIL-STD-202:103B	1. Ta=65□±5□ 2. RH=90%~95% 3. Tt=240hrs±2hrs	The purpose of this id the resistance of the device which is laid under condition of low temperature for hours.
Thermal Shock Test	MIL-STD-202:107D MIL-STD-750:1051 MIL-STD-883:1011	1. Ta=105□±5□&-40□±5□ (10min)(10min)	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.
Solder Resistance Test	JIS C 7021:A-1 MIL-STD-202:210A MIL-STD-750:2031	1.T.Sol=260□±5□ 2.Dwell time=10±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at ex treme changes in temperature when soldering the lead wire.
Solderability Test	JIS C 7021:A-2 MIL-STD-202:208D MIL-STD-750:2026 MIL-STD-883:2003	1.T.Sol=230□±5□ 2.Dwell time=5±1sec.	This test intended to see soldering well performed or not.



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